

# C Thomidis

## List of Publications by Year in descending order

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Version: 2024-02-01

14  
papers

262  
citations

949033

11  
h-index

1255698

13  
g-index

14  
all docs

14  
docs citations

14  
times ranked

452  
citing authors

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 1  | Phosphorous Diffusion in N <sub>2</sub> -Implanted Germanium during Flash Lamp Annealing: Influence of Nitrogen on Ge Substrate Damage and Capping Layer Engineering. ECS Journal of Solid State Science and Technology, 2017, 6, P418-P428. | 0.9 | 5         |
| 2  | Strong Diffusion Suppression of Low Energy-Implanted Phosphorous in Germanium by N <sub>2</sub> Co-Implantation. ECS Solid State Letters, 2015, 4, P47-P50.  | 1.4 | 11        |
| 3  | Molecular beam epitaxy growth of AlGaIn quantum wells on 6H-SiC substrates with high internal quantum efficiency. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, 02B119.                         | 0.6 | 22        |
| 4  | InGaIn-based LEDs grown by plasma-assisted MBE on (0001) sapphire with GaN QDs in the nucleation layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2309-2311.  | 0.8 | 7         |
| 5  | Growth and properties of near-UV light emitting diodes based on InN/GaN quantum wells. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1070-1073.   | 0.8 | 57        |
| 6  | Growth of InGaN nitride quantum dots and their applications to blue-green LEDs. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2560-2565.  | 0.8 | 28        |
| 7  | InGaIn-based LEDs grown by plasma-assisted MBE on (0001) sapphire with GaN QDs in the nucleation layer. , 2008, 5, 2309.   |     | 1         |
| 8  | Growth of InN films by RF plasma-assisted MBE and cluster beam epitaxy. Journal of Crystal Growth, 2006, 288, 254-260.   | 0.7 | 15        |
| 9  | High power ultraviolet light emitting diodes based on GaN/AlGaIn quantum wells produced by molecular beam epitaxy. Journal of Applied Physics, 2006, 100, 104506.  | 1.1 | 21        |
| 10 | Enhanced internal quantum efficiency and light extraction efficiency from textured GaN/AlGaIn quantum wells grown by molecular beam epitaxy. Journal of Applied Physics, 2006, 99, 064904.   | 1.1 | 22        |
| 11 | Growth and silicon doping of AlGaIn films in the entire alloy composition by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2220-2223.   | 0.8 | 18        |
| 12 | Ultraviolet electroabsorption modulator based on AlGaIn/GaN multiple quantum wells. Journal of Applied Physics, 2005, 97, 123515.  | 1.1 | 22        |
| 13 | Well width dependence of disorder effects on the optical properties of AlGaIn/GaN quantum wells. Applied Physics Letters, 2004, 85, 3068-3070.   | 1.5 | 13        |
| 14 | Investigation of excitons in AlGaIn/GaN multiple quantum wells by lateral photocurrent and photoluminescence spectroscopies. Journal of Applied Physics, 2004, 95, 3495-3502.  | 1.1 | 20        |